

## **IN THE CLAIMS:**

Please cancel claim 7 without prejudice or disclaimer of the subject matter thereof.

### **Amendments to the Claims**

#### **Listing of Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A plasma processing apparatus to provide plasma processing of a substrate by plasma, said plasma processing apparatus comprising a plasma processing gas supply means, an exhaust means in a plasma process chamber, and a plasma generating means, said plasma generating means further comprises:

a first capacitatively coupled plasma generating means; and

a second electromagnetic wave radiation plasma generating means;

wherein said first capacitatively coupled plasma means includes an opposed plate type electrode consisting of a plurality of mutually isolated conductors oppositely disposed with respect to a stage electrode and a single commonly shared high-frequency power supply means to supply for supplying said high-frequency power to said plurality of isolated conditions of said opposed electrode through a matching box, said first capacitatively coupled plasma generating means being arranged so that a capacitatively coupled plasma discharge is generated between said opposed electrode and said stage electrode;

wherein said second electromagnetic wave radiation plasma generating means comprises insulators disposed between at least a portion of a plasma process chamber which is grounded and said plurality of isolated conductors, respectively, said second electromagnetic wave radiation plasma generating means being arranged so that an electromagnetic wave is radiated from ~~at least a position~~

each of positions between said plurality of isolated conductors which are connected to said matching box by supply of current through ~~at least one~~ each current path of an inductor L and a capacitor C and said grounded plasma process chamber via plasma forming a resonance circuit including ~~at least one of~~ said L and C so as to generate plasma discharge in said plasma process chamber, a resonance of each of said resonance circuit ~~including~~ being controlled by controlling at least one of said L and C ~~being controlled~~; and

wherein said plasma processing apparatus further includes a RF bias circuit which is separated from ground so as to send-supply RF current to the substrate to be processed; and

wherein said first capacitatively coupled generating means and said second electromagnetic wave radiation plasma generating means combine to provide plasma discharge in the plasma process chamber and current of each said resonance circuit is controlled commonly so that plasma distribution controllability is ~~with enhanced plasma distribution controllability.~~

2. (currently amended) A plasma processing apparatus according to claim 1, wherein said second electromagnetic wave radiation plasma generating means is arranged so that said plasma discharge is generated under an ECR condition controlled by a magnetic field formed by ~~coils~~ at least one and said electromagnetic wave is radiated to said plasma process chamber.

3. (previously presented) A plasma processing apparatus according to Claim 1 or 2 further characterized by a means to store a processing procedure to control distribution during plasma processing and a distribution controller controls plasma distribution during plasma processing according to the processing procedure stored in said store means.

Claims 4-6 (canceled)

Claim 7 (canceled)

8. (currently amended) A plasma processing apparatus according to claim 1, further comprising a means to process plasma using the generated plasma, ~~wherein said means to process plasma enables supplying of RF current to the substrate to be processed and includes and further including~~ multiple RF current conducting means installed at a position opposite to a position where the substrate to be processed is mounted, said multiple RF current conducting means being provided with a means to control a ratio of RF current flowing from the substrate to be processed to each of said multiple RF current conducting means.